# International TOR Rectifier

## **AUTOMOTIVE MOSFET**

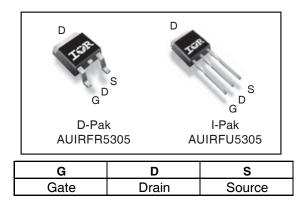
# AUIRFR5305 AUIRFU5305

HEXFET® Power MOSFET

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-			
	V <sub>(BR)DSS</sub>		-55V
	R <sub>DS(on)</sub>	max.	0.065Ω
	I <sub>D</sub>		-31A



## **Features**

- Advanced Planar Technology
- Low On-Resistance
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified \*

## **Description**

Specifically designed for Automotive applications, this Cellular Planar design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

## Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature  $(T_A)$  is  $25^{\circ}C$ , unless otherwise specified.

**Absolute Maximum Ratings** 

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V	-31	
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ -10V	-22	Α
I <sub>DM</sub>	Pulsed Drain Current ①⑥	-110	
P <sub>D</sub> @T <sub>C</sub> = 25°C	Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Thermally limited) ② ⑤	280	mJ
I <sub>AR</sub>	Avalanche Current ① ©	-16	Α
E <sub>AR</sub>	Repetitive Avalanche Energy ①	11	mJ
dv/dt	Peak Diode Recovery dv/dt ③ ⑥	-5.0	V/ns
TJ	Operating Junction and	-55 to + 175	
T <sub>STG</sub>	Storage Temperature Range		°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

#### Thermal Resistance

	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case		1.4	
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) **		50	°C/W
$R_{\theta JA}$	Junction-to-Ambient ***		110	

HEXFET® is a registered trademark of International Rectifier.

<sup>\*</sup>Qualification standards can be found at http://www.irf.com/



## Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-55		_	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient		-0.034	_	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance			0.065	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -16A ⊕
$V_{GS(th)}$	Gate Threshold Voltage	-2.0		-4.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$
gfs	Forward Transconductance	8.0		_	S	$V_{DS} = -25V, I_{D} = -16A$
I <sub>DSS</sub>	Drain-to-Source Leakage Current			-25	1	$V_{DS} = -55V, V_{GS} = 0V$
				-250	μΑ	$V_{DS} = -44V, V_{GS} = 0V, T_{J} = 150$ °C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage			100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage			-100	IIA	$V_{GS} = 20V$

# Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

<u>Dynamic i</u>	Liectrical Characteristics @ 1j = 25 C (u					
	Parameter	Min.	Тур.	Max.	Units	Conditions
$Q_g$	Total Gate Charge			63		I <sub>D</sub> = -16A
$Q_{gs}$	Gate-to-Source Charge			13	nC	$V_{DS} = -44V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge			29		V <sub>GS</sub> = -10V See Fig.6 and 13 ⊕ ©
t <sub>d(on)</sub>	Turn-On Delay Time		14			$V_{DD} = -28V$
t <sub>r</sub>	Rise Time		66		]	$I_{D} = -16A$
t <sub>d(off)</sub>	Turn-Off Delay Time		39		ns	$R_G = 6.8 \Omega$
t <sub>f</sub>	Fall Time		63		Ī	$R_D = 1.6 \Omega$ See Fig.10 $\oplus$ $\odot$
L <sub>D</sub>	Internal Drain Inductance		4.5			Between lead,
1 -	Internal Source Inductance				nH	6mm (0.25in.) from package
L <sub>S</sub>	internal Source mudciance		7.5			and center of die contact
C <sub>iss</sub>	Input Capacitance		1200			$V_{GS} = 0V$
C <sub>oss</sub>	Output Capacitance		520		pF	$V_{DS} = -25V$
C <sub>rss</sub>	Reverse Transfer Capacitance		250			f = 1.0MHz,see Fig.5 ©

## **Diode Characteristics**

	Parameter	Min.	Тур.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)			-31		MOSFET symbol showing the
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①			-110		integral reverse p-n junction diode.
$V_{SD}$	Diode Forward Voltage			-1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -16A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time		71	110	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -16A
Q <sub>rr</sub>	Reverse Recovery Charge		170	250	nC	di/dt = 100A/µs ⊕⑥

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- $^{\odot}$  V<sub>DD</sub> = -25V, starting T<sub>J</sub> = 25°C, L = 2.1mH R<sub>G</sub> = 25 $\Omega$ , I<sub>AS</sub> = -16A. (See Figure 12)

- © Uses IRF5305 data and test conditions.

For recommended footprint and soldering techniques refer to application note #AN-994.

<sup>\* \*</sup>When mounted on 1" square PCB (FR-4 or G-10 Material).

<sup>\*\*\*</sup> Uses typical socket mount.

# Qualification Information<sup>†</sup>

		Automotive			
		(per AEC-Q101) ††			
Qualification Level  Comments: This part number(s) passed Automotive qualification level is qualification level is qualification of the higher Automotive level.			l and Consumer qualification level is granted by		
Moisture Sensitivity Level		D PAK MSL1			
		I-PAK	N/A		
	Machine Model	Class M2 (200V)			
		( per AEC-Q101-002)			
ECD	Human Body Model	Class H1B (1000V)			
ESD		(per AEC-Q101-001)			
	Charged Device	Class C5 (1125V)			
Model		(per AEC-Q101-005)			
RoHS Complia	nt		Yes		

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

<sup>††</sup> Exceptions to AEC-Q101 requirements are noted in the qualification report.

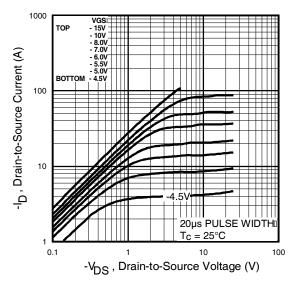


Fig 1. Typical Output Characteristics

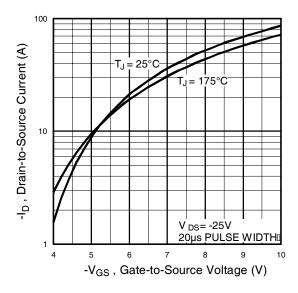


Fig 3. Typical Transfer Characteristics

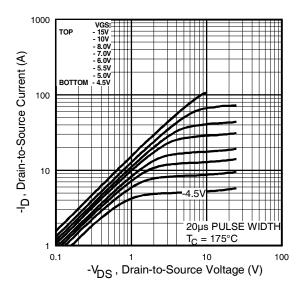
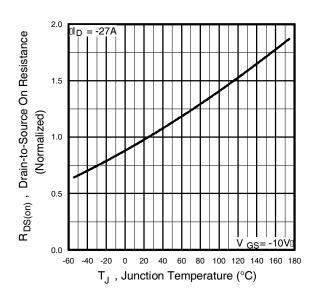
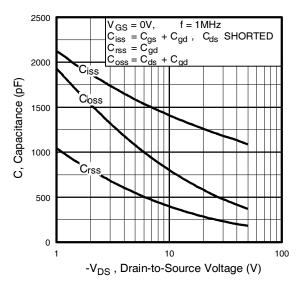


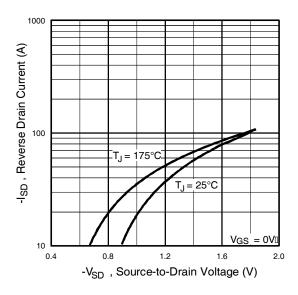
Fig 2. Typical Output Characteristics



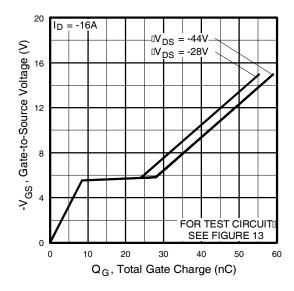
**Fig 4.** Normalized On-Resistance Vs. Temperature



**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

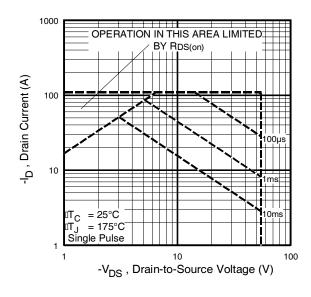


Fig 8. Maximum Safe Operating Area

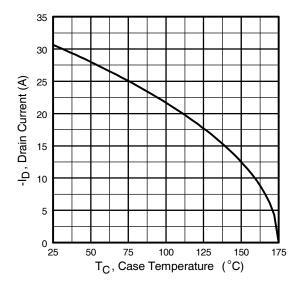


Fig 9. Maximum Drain Current Vs. Case Temperature

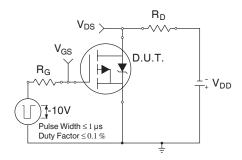


Fig 10a. Switching Time Test Circuit

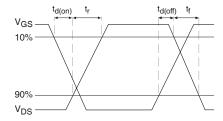


Fig 10b. Switching Time Waveforms

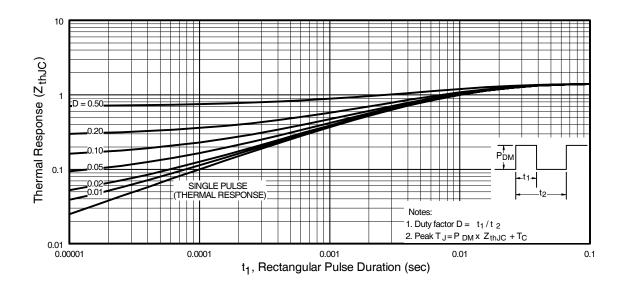


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

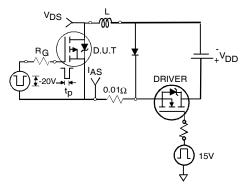


Fig 12a. Unclamped Inductive Test Circuit

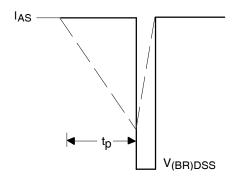


Fig 12b. Unclamped Inductive Waveforms

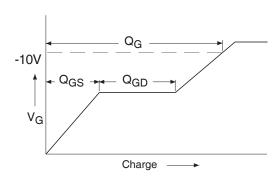


Fig 13a. Basic Gate Charge Waveform

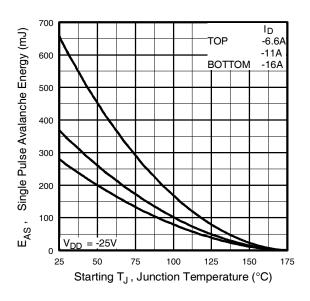


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

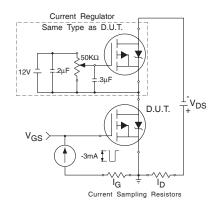
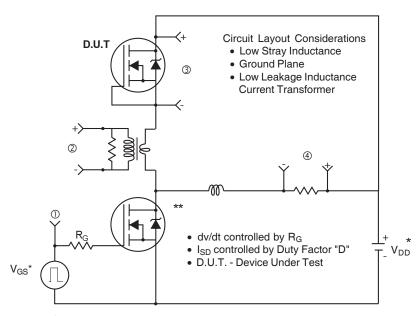
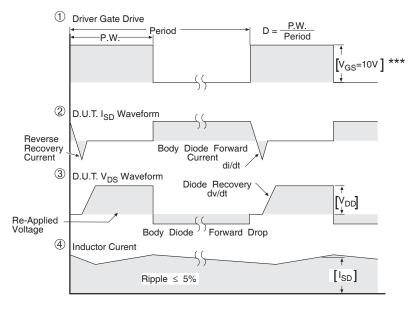


Fig 13b. Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



- \* Reverse Polarity for P-Channel
- \*\* Use P-Channel Driver for P-Channel Measurements



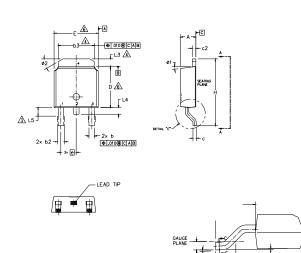
\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

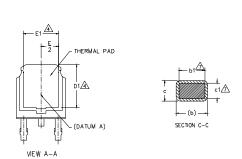
Fig 14. For P-Channel HEXFETS

# AUIRFR/U5305

# D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)





DETAIL "C" ROTATED 90" CW SCALE: 20:1

甲盒 SEATING PLANE

#### NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
- ⚠- LEAD DIMENSION UNCONTROLLED IN L5.
- A- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH, MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- \_\_\_\_ DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

S Y			Z			
M B O	MILLIM	ETERS	INC	HES	NO TES	
L	MIN,	MAX.	MIN.	MAX.	S	
Α	2.18	2.39	.086	.094		
A1	-	0,13	-	.005		
b	0.64	0.89	.025	.035		
ь1	0.65	0.79	.025	.031	7	
b2	0.76	1,14	.030	.045		
b3	4.95	5.46	.195	.215	4	
С	0.46	0,61	.018	.024		
c1	0.41	0.56	.016	.022	7	
c2	0.46	0.89	.018	.035		
D	5.97	6.22	.235	.245	6	
D1	5,21	-	.205	-	4	
Ε	6.35	6.73	.250	.265	6	
E1	4.32	-	.170	-	4	
е	2.29	BSC	.090	BSC		
Н	9.40	10.41	.370	.410		
L	1,40	1,78	.055	.070		
L1	2.74	BSC	.108	REF.		
L2	0.51	BSC	.020 BSC			
L3	0.89	1.27	.035	.050	4	
L4	-	1.02	-	.040		
L5	1,14	1.52	.045	.060	3	
Ø	0*	10*	0,	10*		
ø1	0.	15*	0.	15*		
ø2	25*	35*	25*	35*		

#### LEAD ASSIGNMENTS

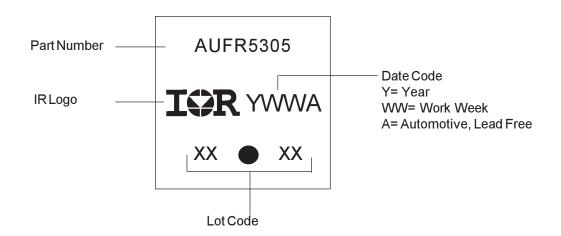
#### HEXFET

- 1.- GATE 2.- DRAIN
- 3.- SOURCE 4.- DRAIN

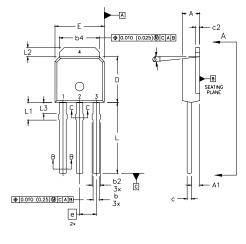
#### IGBT & CoPAK

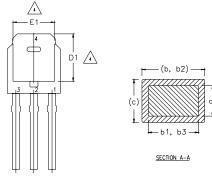
- 2.- COLLECTOR
- 3. EMITTER 4. COLLECTOR

# D-Pak (TO-252AA) Part Marking Information



# I-Pak (TO-251AA) Package Outline (Dimensions are shown in millimeters (inches)





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- DIMENSIONING AND IOLERANCING PER ASME Y14.5 M- 1994.
  DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  DIMENSION D & E DO NOT INCLUDE MOLD FLASH, MOLD FLASH SHALL NOT EXCEED
  0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST
  EXTREMES OF THE PLASTIC BODY.
  THERMAL PAD CONTOUR OPTION WITHIN DIMENSION 64, L2, E1 & D1.
- LEAD DIMENSION UNCONTROLLED IN L3.
- DIMENSION 61, 63 APPLY TO BASE METAL ONLY. OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA, CONTROLLING DIMENSION: INCHES,

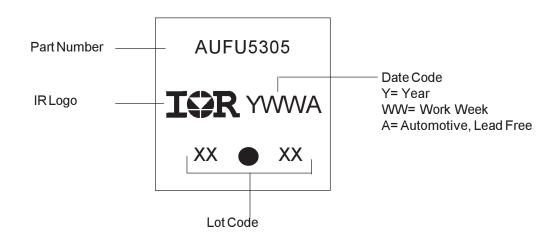
		DIMEN	SIONS		
SYMBOL	MILLIM	ETERS	INC	HES	
	MIN.	MAX.	MIN.	MAX.	NOTES
A	2,18	2,39	0.086	.094	
A1	0,89	1,14	0,035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1,14	0.030	0.045	
b3	0.76	1,04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
с	0.46	0.61	0.01B	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.01B	0.035	
D	5,97	6,22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4,32	-	0,170	-	4
e	2.	29	0.090	BSC	
L	8.89	9.60	0.350	0.380	
Lf	1,91	2,29	0,075	0.090	
L2	0.89	1,27	0.035	0.050	4
L3	1,14	1,52	0,045	0.060	5
ø1	0"	15"	0,	15*	

LEAD ASSIGNMENTS

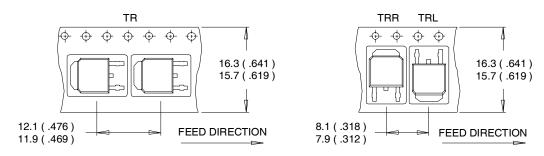
**HEXFET** 1.- GATE

- 2.- DRAIN
- 3.- SOURCE 4.- DRAIN

I-Pak (TO-251AA) Part Marking Information

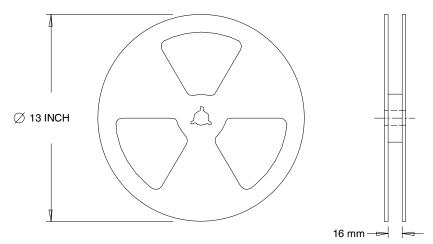


# D-Pak (TO-252AA) Tape & Reel Information



## NOTES:

- CONTROLLING DIMENSION : MILLIMETER.
   ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
- 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



## NOTES:

1. OUTLINE CONFORMS TO EIA-481.

# **Ordering Information**

Base part	Package Type	Standard Pack		Complete Part Number
-		Form	Quantity	
AUIRFR5305	DPak	Tube	75	AUIRFR5305
		Tape and Reel	2000	AUIRFR5305TR
		Tape and Reel Left	3000	AUIRF5305TRL
		Tape and Reel Right	3000	AUIRF5305TRR
AUIRFU5305	IPak	Tube	75	AUIRFU5305

International

TOR Rectifier

# AUIRFR/U5305

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For technical support, please contact IR's Technical Assistance Center http://www.irf.com/technical-info/

## **WORLDHEADQUARTERS:**

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